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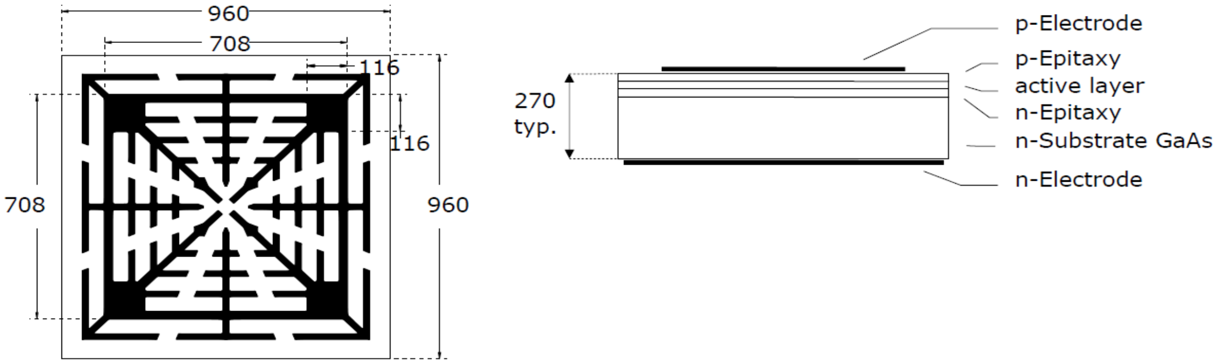
Data Sheet Prelimanary

LED Chip Infrared EOLC-1140-11

Rev. 01, 2017

Radiation	Type	Electrodes
Infrared	InGaAs/GaAs, MQW	P (anode) up



Electrodes / metallization - Au alloy

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=100 mA	V_F		1.05	1.25	V
Forward voltage	I_F=350 mA	V_F		1.15	1.35	V
Reverse current	I_R=5 V	I_R			10	µA
Radiant power*	I_F=50 mA	Φ_e	2	2.7		mW
Radiant intensity	I_F=350 mA	I_e		4		mW/sr
Peak wavelength	I_F=350 mA	λ_p	1120	1140	1160	nm
FWHM	I_F=350 mA	$\Delta\lambda_{0.5}$		60		nm
Switching time	I_F=350 mA	t_r, t_f		20		ns

*Measured on gold plate

Packing

Chips on adhesive film with wire-bond side top

Art. No. 113 055

RoHS COMPLIANT Pb Pb-Free